

Inventor: Ji Ung Lee et al.

Title: "Field Effect Transistor Fabrication Methods, Field Emission Device  
Fabrication Methods, and Field Emission Device Operational Methods"

Assignee: Micron Technology, Inc.

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JC996 S. PTO  
10/072415



**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 09/260,231, filed March 1, 1999. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated:

2/5/02

By:

James D. Shaurette  
Reg. No. 39,833

Form PTO-1449

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## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclasses	Filing Date If Appropriate
	AA	5,482,870	01/09/96	Inoue			
	AB	5,372,973	12/13/94	Doan et al.			
	AC	5,229,331	07/20/93	Doan et al.			
	AD	5,210,472	05/11/93	Casper et al.			
	AE	4,988,638	01/29/91	Huang et al.			
	AF	6,057,555	5/2/00	Reedy et al.			
	AG	5,710,478	1/20/98	Kanemaru et a.			
	AH	6,020,683	2/1/00	Cathey, Jr. et al.			
	AI	6,249,327 B1	6/19/01	Murade et al.			
	AJ						
	AK						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclasses	Translation	
							Yes	No
	AL	5-114734	05/07/93	Japan			X	
	AM	3-194937	08/26/91	Japan			X	
	AN	3-159250	07/09/91	Japan			X	
	AO	A-2-143462	11/24/88	Japan			X	
	AP	61-252667	11/10/86	Japan			X	
	AQ	A-57-85262	11/17/80	Japan			X	

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuitry on Glass,
			F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.I. Milne, Appl. Phys. Lett. 71 - 10/06/97, pages 2002-2004, 1997 American Institute of Physics.
	AS		Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Griep, Mat. Res. Soc. Symp. Proc. 149, pages 283-288, 1989 Materials Research Society.
	AT		

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.